

Title (en)
Polishing method

Title (de)
Polierverfahren

Title (fr)
Procédé de polissage

Publication
EP 1308243 A1 20030507 (EN)

Application
EP 02025724 A 19950913

Priority
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Abstract (en)
The present invention relates to a semiconductor device manufacturing method, comprising the steps of: forming on a substrate a first insulating film having an opening; forming a first wiring layer extending from the interior of said opening onto said first insulating layer; forming on said first wiring layer a second insulating film thicker than the first wiring layer polishing and thereby levelling said second insulating film, forming a second wiring layer on the levelled second insulating film; whereby said step of levelling said second insulating film includes: using at least two polishing tools stepwise, wherein the modulus of elasticity of the polishing tool used first, i.e., the first polishing tool, is smaller than that of the polishing tool used next, i.e., the second polishing tool. <IMAGE>

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Citation (search report)
• [A] EP 0272531 A1 19880629 - SUMITOMO ELECTRIC INDUSTRIES [JP], et al
• [A] US 5361545 A 19941108 - NAKAMURA YOSHIO [JP]
• [DA] PATENT ABSTRACTS OF JAPAN vol. 013, no. 240 (E - 767) 6 June 1989 (1989-06-06)

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